

40V DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| $V_{(BR)DSS}$ | $R_{DS(on) Max}$ | I_D $T_A = +25^\circ C$ |
|---------------|-------------------------|------------------------------|
| -40V | 50mΩ @ $V_{GS} = -10V$ | -5.2A |
| | 79mΩ @ $V_{GS} = -4.5V$ | -4.1A |

Description

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.


Applications

- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

Features and Benefits

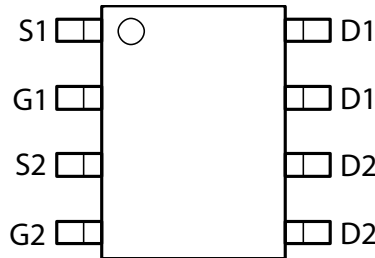
- Low On-Resistance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

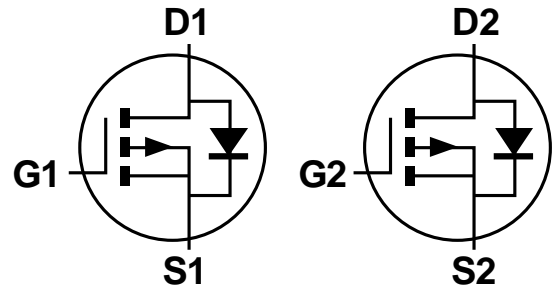
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See diagram below
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208 
- Weight: 0.074 grams (approximate)



Top View



Top View



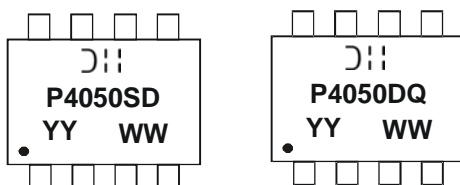
Equivalent Circuit


Ordering Information (Note 4)

| Part Number | Qualification | Case | Packaging |
|----------------|---------------|------|--------------------|
| DMP4050SSD-13 | Standard | SO-8 | 2500 / Tape & Reel |
| DMP4050SSDQ-13 | Automotive | SO-8 | 2500 / Tape & Reel |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



 = Manufacturer's Marking
 P4050SD = Product Type Marking Code for DMP4050SSD-13
 P4050DQ = Product Type Marking Code for DMP4050SSDQ-13
 YYWW = Date Code Marking
 YY = Year (ex: 09 = 2009)
 WW = Week (01-53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

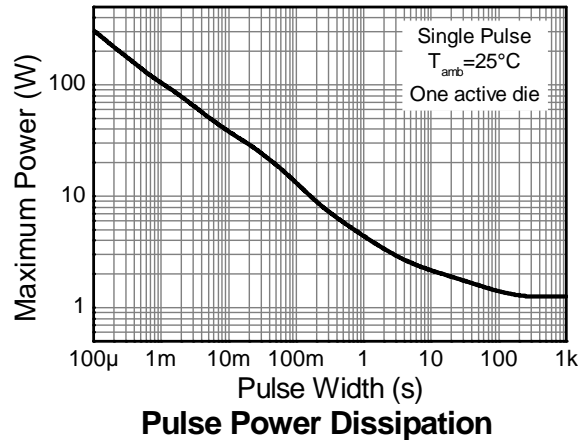
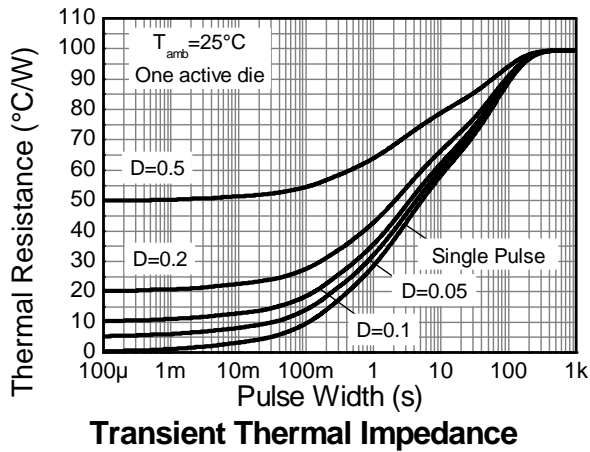
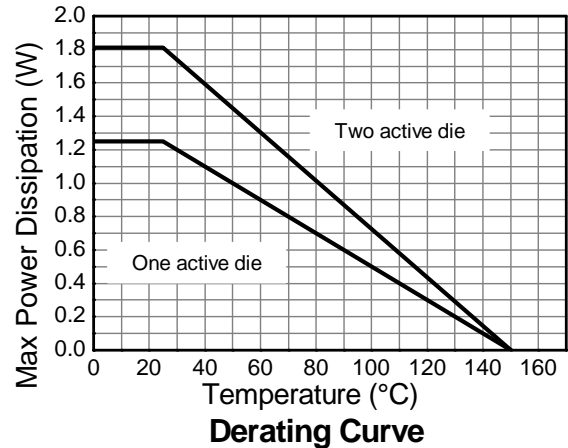
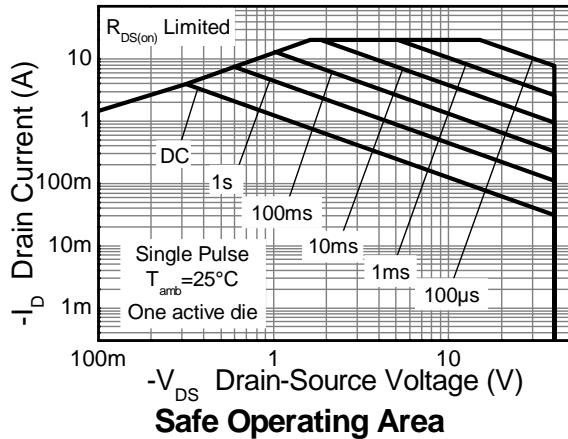
| Characteristic | | | Symbol | Value | Unit |
|--|-----------------------|---|-----------|----------|------|
| Drain-Source Voltage | | | V_{DSS} | -40 | V |
| Gate-Source Voltage | | | V_{GS} | ± 20 | V |
| Continuous Drain Current | $V_{GS} = 10\text{V}$ | (Notes 9 & 11) | I_D | -5.2 | A |
| | | $T_A = +70^\circ\text{C}$ (Notes 7 & 9) | | -4.2 | |
| | | (Notes 6 & 9) | | -4.0 | |
| Pulsed Drain Current | $V_{GS} = 10\text{V}$ | (Notes 8 & 9) | I_{DM} | -20.0 | A |
| Continuous Source Current (Body Diode) | | | I_S | -3.2 | A |
| Pulsed Source Current (Body Diode) | | | I_{SM} | -20.0 | A |

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | | Symbol | Value | Unit |
|---|----------------|-----------------|-------------|---------------------------|
| Power dissipation Linear derating factor | (Notes 6 & 9) | P_D | 1.25 | W mW/ $^\circ\text{C}$ |
| | | | 10.0 | |
| | (Notes 6 & 10) | | 1.8 | |
| | | | 14.3 | |
| Thermal Resistance, Junction to Ambient | (Notes 7 & 9) | $R_{\theta JA}$ | 2.14 | $^\circ\text{C/W}$ |
| | (Notes 6 & 9) | | 100 | |
| | (Notes 6 & 10) | | 70 | |
| | (Notes 7 & 9) | 58 | | |
| Thermal Resistance, Junction to Lead | (Notes 9 & 11) | $R_{\theta JL}$ | 53 | |
| Operating and storage temperature range | | T_J, T_{STG} | -55 to +150 | $^\circ\text{C}$ |

- Notes:
5. AEC-Q101 V_{GS} maximum is $\pm 16\text{V}$.
 6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 7. Same as note (3), except the device is measured at $t \leq 10$ sec.
 8. Same as note (3), except the device is pulsed with $D = 0.02$ and pulse width 300 μs . The pulse current is limited by the maximum junction temperature.
 9. For a dual device with one active die.
 10. For a device with two active die running at equal power.
 11. Thermal resistance from junction to solder-point (at the end of the drain lead).

Thermal Characteristics

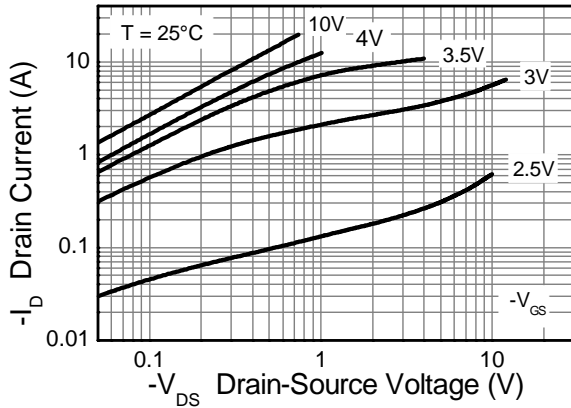


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

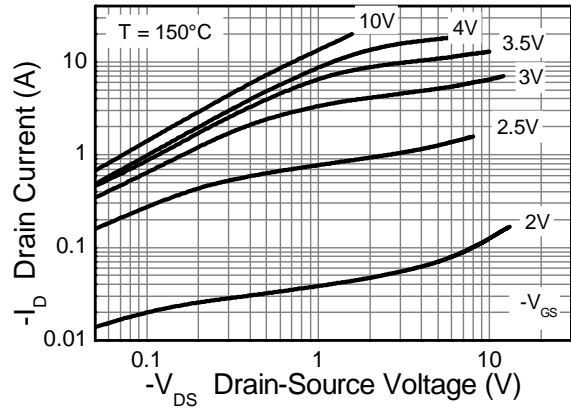
| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---|---------------------|------|-------|-------|------|---|
| OFF CHARACTERISTICS | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -40 | — | — | V | I _D = -250μA, V _{GS} = 0V |
| Zero Gate Voltage Drain Current | I _{DSS} | — | — | -0.5 | μA | V _{DS} = -40V, V _{GS} = 0V |
| Gate-Source Leakage | I _{GSS} | — | — | ±100 | nA | V _{GS} = ±20V, V _{DS} = 0V |
| ON CHARACTERISTICS | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | -1.0 | — | -3.0 | V | I _D = -250μA, V _{DS} = V _{GS} |
| Static Drain-Source On-Resistance (Note 12) | R _{DS(ON)} | — | 0.038 | 0.050 | Ω | V _{GS} = -10V, I _D = -6A |
| | | | 0.055 | 0.079 | | V _{GS} = -4.5V, I _D = -5A |
| Forward Transconductance (Notes 12 & 13) | g _{fs} | — | 14 | — | S | V _{DS} = -15V, I _D = -6A |
| Diode Forward Voltage (Note 12) | V _{SD} | — | -0.86 | -1.2 | V | I _S = -6A, V _{GS} = 0V |
| Reverse recovery time (Note 13) | t _{rr} | — | 18 | — | ns | I _S = -2A, di/dt = 100A/μs |
| Reverse recovery charge (Note 13) | Q _{rr} | — | 12.7 | — | nC | |
| DYNAMIC CHARACTERISTICS (Note 13) | | | | | | |
| Input Capacitance | C _{iSS} | — | 674 | — | pF | V _{DS} = -20V, V _{GS} = 0V f = 1MHz |
| Output Capacitance | C _{oSS} | — | 115 | — | pF | |
| Reverse Transfer Capacitance | C _{rSS} | — | 67.7 | — | pF | |
| Total Gate Charge (Note 14) | Q _g | — | 6.9 | — | nC | V _{GS} = -4.5V |
| Total Gate Charge (Note 14) | Q _g | — | 13.9 | — | nC | V _{GS} = -10V |
| Gate-Source Charge (Note 14) | Q _{gs} | — | 2 | — | nC | |
| Gate-Drain Charge (Note 14) | Q _{gd} | — | 3.4 | — | nC | |
| Turn-On Delay Time (Note 14) | t _{D(on)} | — | 1.9 | — | ns | V _{DD} = -20V, V _{GS} = -10V I _D = -1A, R _G ≅ 6.0Ω |
| Turn-On Rise Time (Note 14) | t _r | — | 3.1 | — | ns | |
| Turn-Off Delay Time (Note 14) | t _{D(off)} | — | 31.5 | — | ns | |
| Turn-Off Fall Time (Note 14) | t _f | — | 12.6 | — | ns | |

- Notes: 12. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
13. For design aid only, not subject to production testing.
14. Switching characteristics are independent of operating junction temperatures.

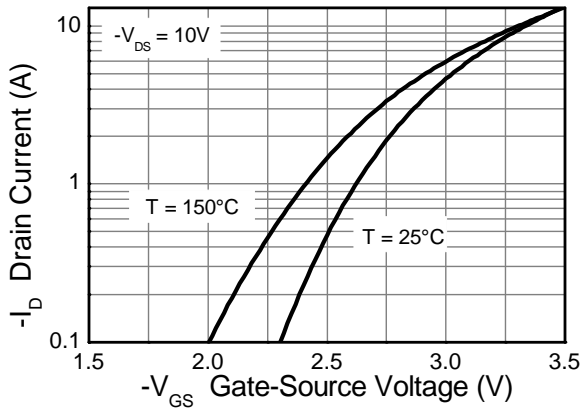
Typical Characteristics



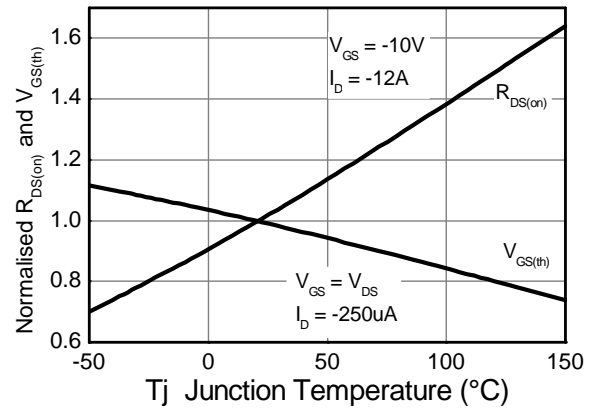
Output Characteristics



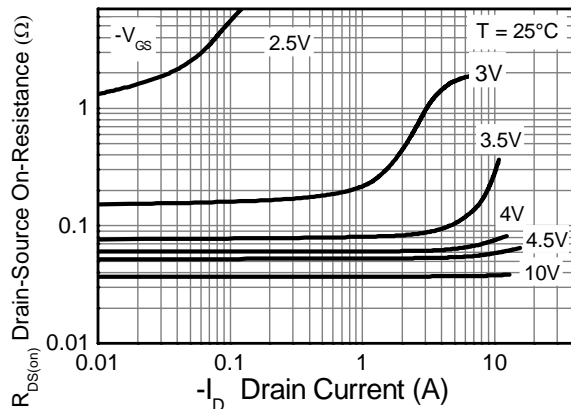
Output Characteristics



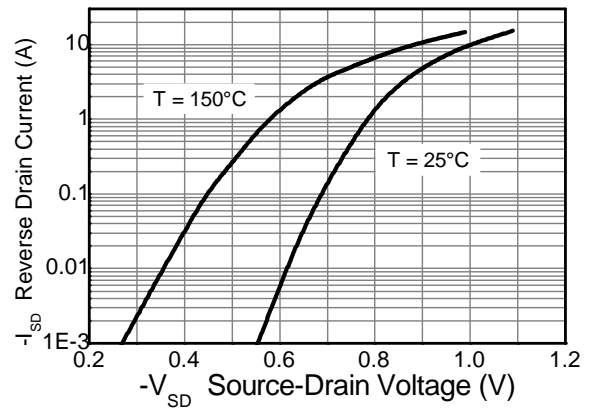
Typical Transfer Characteristics



Normalised Curves v Temperature

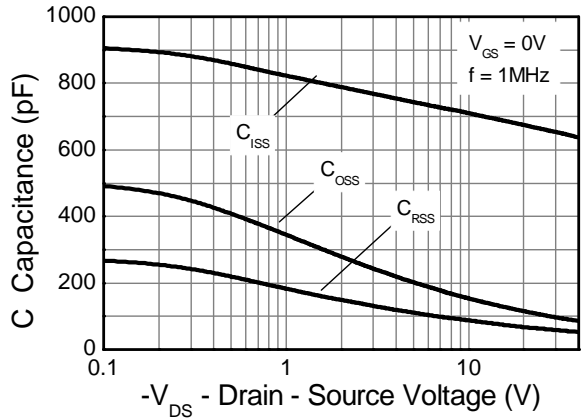


On-Resistance v Drain Current

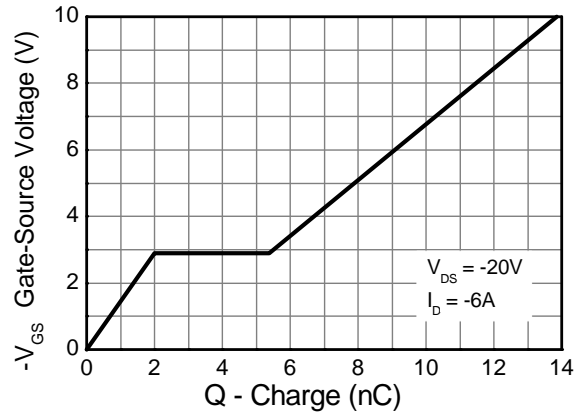


Source-Drain Diode Forward Voltage

Typical Characteristics – (cont.)

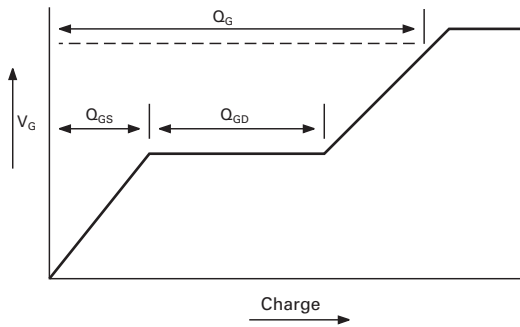


Capacitance v Drain-Source Voltage

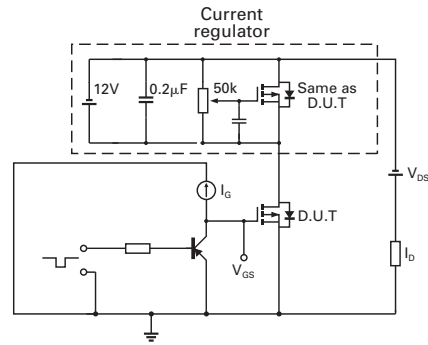


Gate-Source Voltage v Gate Charge

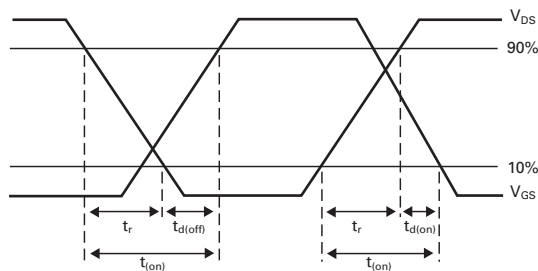
Test Circuits



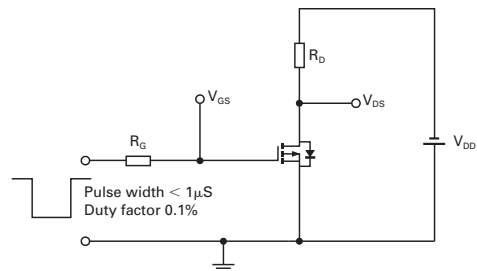
Basic gate charge waveform



Gate charge test circuit



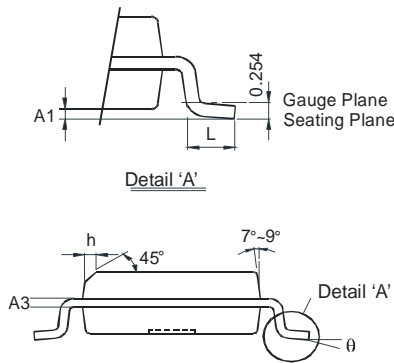
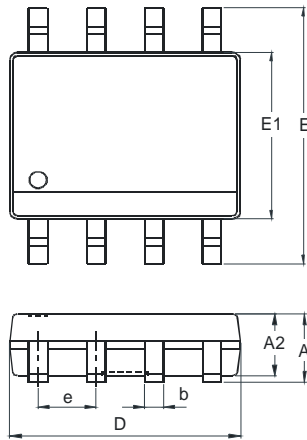
Switching time waveforms



Switching time test circuit

Package Outline Dimensions

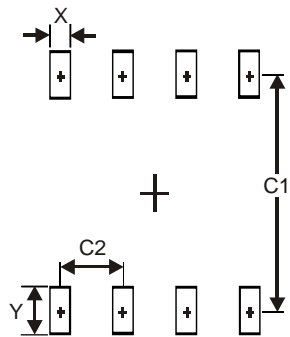
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



| SO-8 | | |
|----------------------|----------|------|
| Dim | Min | Max |
| A | - | 1.75 |
| A1 | 0.10 | 0.20 |
| A2 | 1.30 | 1.50 |
| A3 | 0.15 | 0.25 |
| b | 0.3 | 0.5 |
| D | 4.85 | 4.95 |
| E | 5.90 | 6.10 |
| E1 | 3.85 | 3.95 |
| e | 1.27 Typ | |
| h | - | 0.35 |
| L | 0.62 | 0.82 |
| θ | 0° | 8° |
| All Dimensions in mm | | |

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| X | 0.60 |
| Y | 1.55 |
| C1 | 5.4 |
| C2 | 1.27 |

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